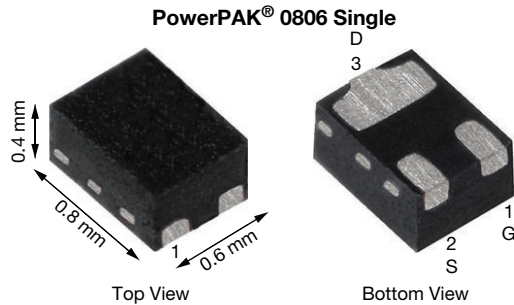


## N-Channel 12 V (D-S) MOSFET



### FEATURES

- TrenchFET® power MOSFET
- Ultra small 0.8 mm x 0.6 mm outline
- Ultra thin 0.4 mm max. height
- Typical ESD protection 1500 V (HBM)
- 1.2 V rated  $R_{DS(on)}$
- 100 %  $R_g$  tested
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)

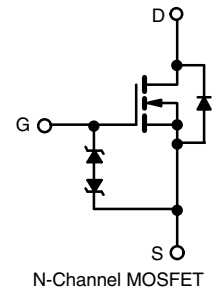


**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

PRODUCT SUMMARY	
$V_{DS}$ (V)	12
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 4.5$ V	0.34
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 2.5$ V	0.4
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 1.8$ V	0.55
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 1.5$ V	1.2
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 1.2$ V	2.5
$Q_g$ typ. (nC)	0.47
$I_D$ (A)	0.5 <sup>a, f</sup>
Configuration	Single

### APPLICATIONS

- Load switch
- High speed switching
- DC/DC converters
- Battery-operated and mobile devices



ORDERING INFORMATION	
Package	PowerPAK 0806
Lead (Pb)-free and halogen-free	SiUD412ED-T1-GE3

#### Note

- The lead finish is NiPdAu and classed as E4 finish

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage	$V_{DS}$	12	V	
Gate-source voltage	$V_{GS}$	$\pm 5$	V	
Continuous drain current / $T_J = 150$ °C)	$I_D$	$T_A = 25$ °C	0.5 <sup>a, f</sup>	A
		$T_A = 70$ °C	0.5 <sup>a, f</sup>	
		$T_A = 25$ °C	0.5 <sup>b</sup>	
		$T_A = 70$ °C	0.5 <sup>b</sup>	
Pulsed drain current ( $t = 100$ $\mu$ s)	$I_{DM}$	1.5	A	
Continuous source-drain diode current	$I_S$	$T_A = 25$ °C	0.5 <sup>a, f</sup>	A
		$T_A = 70$ °C	0.37 <sup>b</sup>	
Maximum power dissipation	$P_D$	$T_A = 25$ °C	1.25 <sup>a</sup>	W
		$T_A = 70$ °C	0.8 <sup>a</sup>	
		$T_A = 25$ °C	0.37 <sup>b</sup>	
		$T_A = 70$ °C	0.24 <sup>b</sup>	
Operating junction and storage temperature range	$T_J, T_{stg}$	-55 to +150	°C	
Soldering recommendations (peak temperature) <sup>c</sup>		260	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient <sup>a, d</sup>	$R_{thJA}$	80	100	°C/W
Maximum junction-to-ambient <sup>b, e</sup>	$R_{thJA}$	265	335	

#### Notes

- Surface mounted on 1" x 1" FR4 board with full copper,  $t = 5$  s
- Surface mounted on 1" x 1" FR4 board with minimum copper,  $t = 5$  s
- Refer to IPC / JEDEC® (J-STD-020), no manual or hand soldering
- Maximum under steady state conditions is 135 °C/W
- Maximum under steady state conditions is 400 °C/W
- Package limited



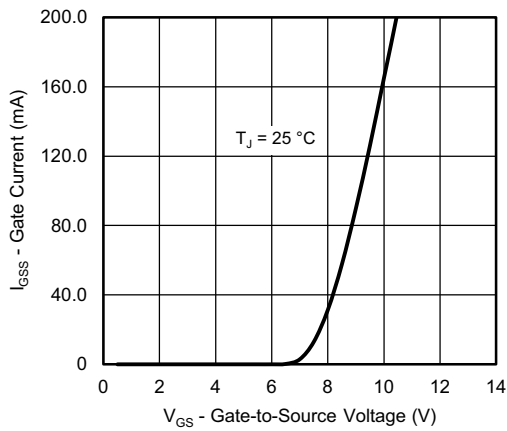
SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	12	-	-	V
V <sub>DS</sub> temperature coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	I <sub>D</sub> = 250 μA	-	9	-	mV/°C
V <sub>GS(th)</sub> temperature coefficient	ΔV <sub>GS(th)</sub> /T <sub>J</sub>		-	-1	-	
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	0.35	-	0.9	V
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 4.5 V	-	-	± 10	μA
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 12 V, V <sub>GS</sub> = 0 V	-	-	1	
		V <sub>DS</sub> = 12 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C	-	-	10	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 5 V, V <sub>GS</sub> = 4.5 V	1	-	-	A
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 0.5 A	-	0.27	0.34	Ω
		V <sub>GS</sub> = 2.5 V, I <sub>D</sub> = 0.2 A	-	0.31	0.4	
		V <sub>GS</sub> = 1.8 V, I <sub>D</sub> = 0.1 A	-	0.37	0.55	
		V <sub>GS</sub> = 1.5 V, I <sub>D</sub> = 0.1 A	-	0.42	1.2	
		V <sub>GS</sub> = 1.2 V, I <sub>D</sub> = 0.05 A	-	0.55	2.5	
Forward transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 6 V, I <sub>D</sub> = 0.5 A	-	1.6	-	S
<b>Dynamic <sup>b</sup></b>						
Input capacitance	C <sub>ISS</sub>	V <sub>DS</sub> = 6 V, V <sub>GS</sub> = 0 V, f = 1 MHz	-	21	-	pF
Output capacitance	C <sub>OSS</sub>		-	13	-	
Reverse transfer capacitance	C <sub>RSS</sub>		-	7	-	
Total gate charge	Q <sub>g</sub>	V <sub>DS</sub> = 6 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 0.5 A	-	0.47	0.71	nC
Gate-source charge	Q <sub>gs</sub>	V <sub>DS</sub> = 6 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 0.5 A	-	0.04	-	
Gate-drain charge	Q <sub>gd</sub>		-	0.09	-	
Gate resistance	R <sub>g</sub>	f = 1 MHz	3	15	30	Ω
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> = 6 V, R <sub>L</sub> = 12 Ω, I <sub>D</sub> ≅ 0.5 A, V <sub>GEN</sub> = 4.5 V, R <sub>g</sub> = 1 Ω	-	2	5	ns
Rise time	t <sub>r</sub>		-	20	40	
Turn-off delay time	t <sub>d(off)</sub>		-	17	35	
Fall time	t <sub>f</sub>		-	10	20	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous source-drain diode current	I <sub>S</sub>	T <sub>A</sub> = 25 °C	-	-	0.5 <sup>c</sup>	A
Pulse diode forward current	I <sub>SM</sub>		-	-	1.5	
Body diode voltage	V <sub>SD</sub>	I <sub>S</sub> = 0.5 A, V <sub>GS</sub> = 0 V	-	0.7	1.2	V
Body diode reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> = 0.5 A, di/dt = 100 A/μs, T <sub>J</sub> = 25 °C	-	15	30	ns
Body diode reverse recovery charge	Q <sub>rr</sub>		-	3	6	nC
Reverse recovery fall time	t <sub>a</sub>		-	12.5	-	ns
Reverse recovery rise time	t <sub>b</sub>		-	2.5	-	

**Notes**

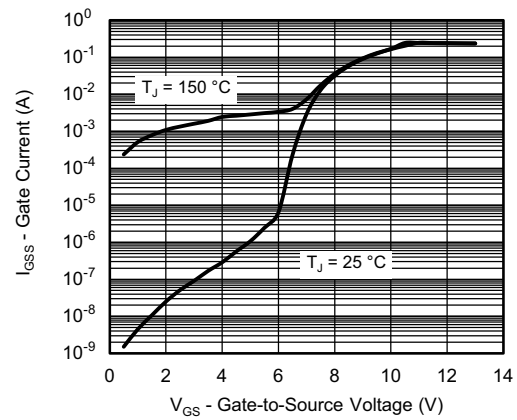
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
- b. Guaranteed by design, not subject to production testing
- c. Surface mounted on 1" x 1" FR4 board with full copper, t = 5 s

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

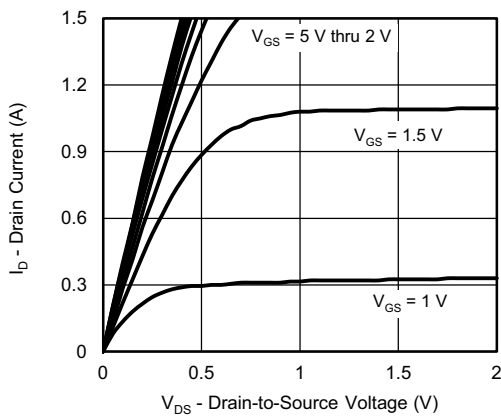
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



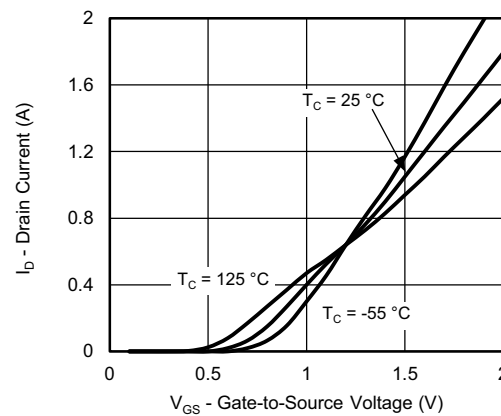
**Gate-Current vs. Gate-Source Voltage**



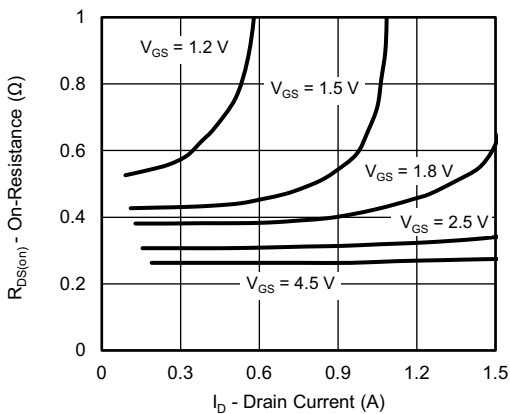
**Gate-Current vs. Gate-Source Voltage**



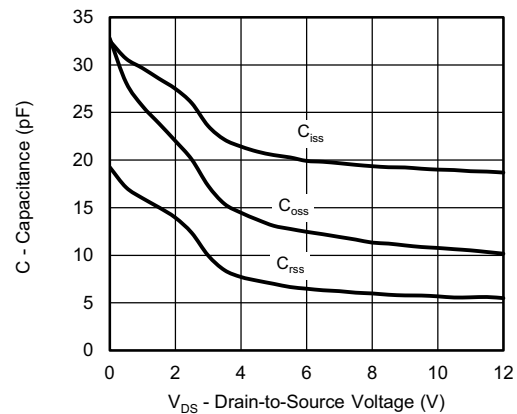
**Output Characteristics**



**Transfer Characteristics**

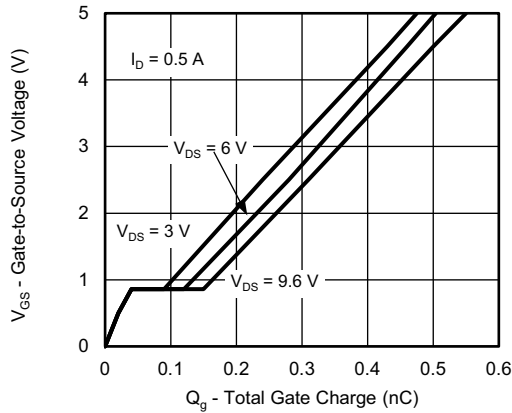


**On-Resistance vs. Drain Current and Gate Voltage**

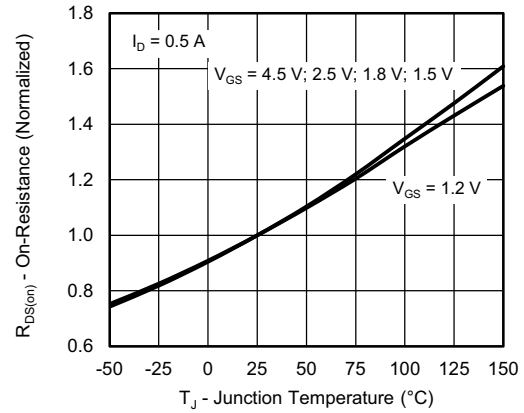


**Capacitance**

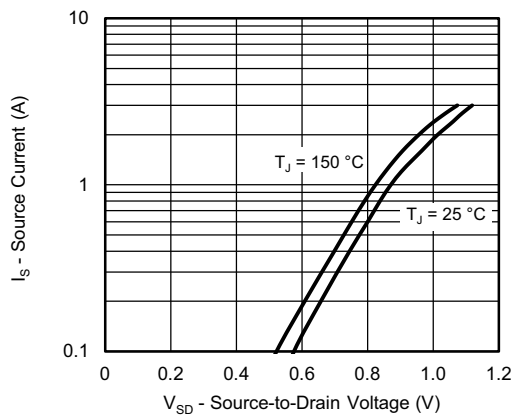
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



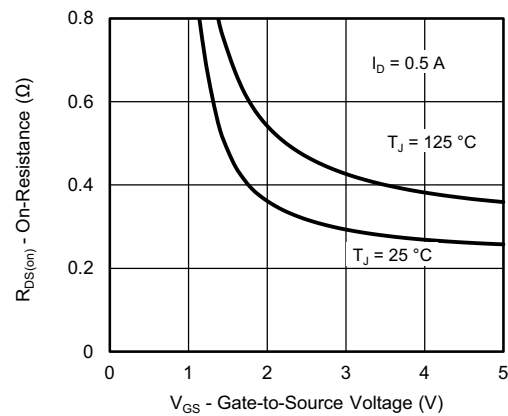
**Gate Charge**



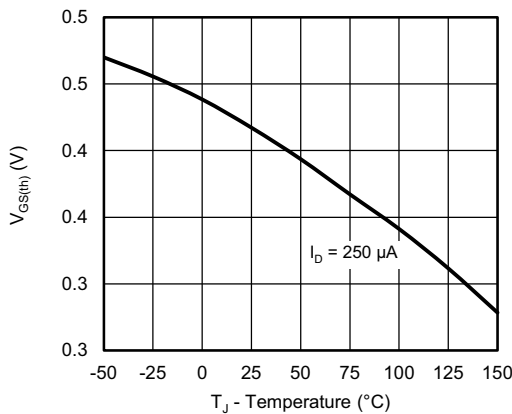
**On-Resistance vs. Junction Temperature**



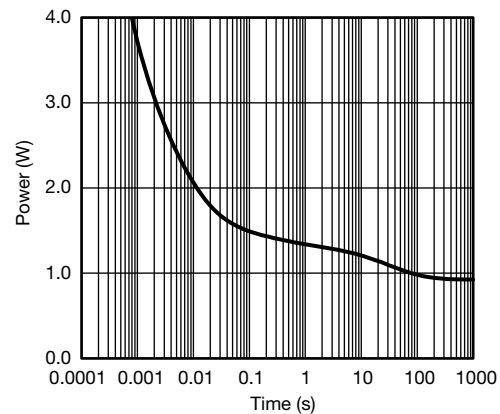
**Source-Drain Diode Forward Voltage**



**On-Resistance vs. Gate-to-Source Voltage**



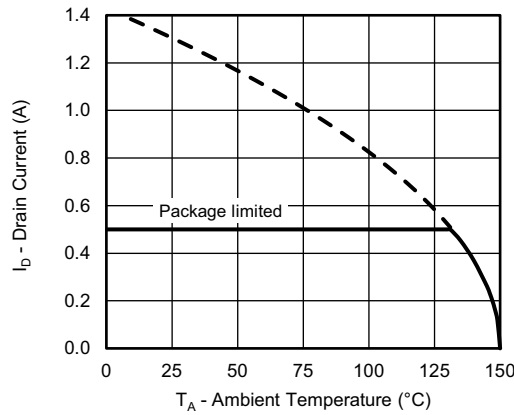
**Threshold Voltage**



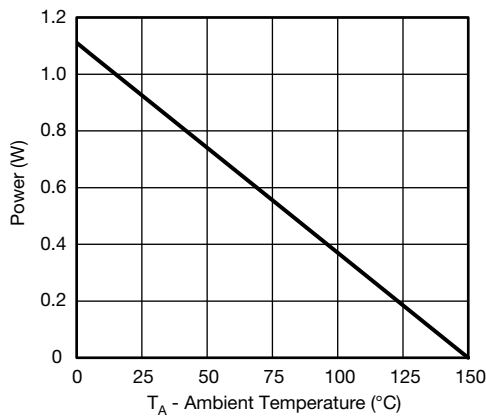
**Single Pulse Power, Junction-to-Ambient**



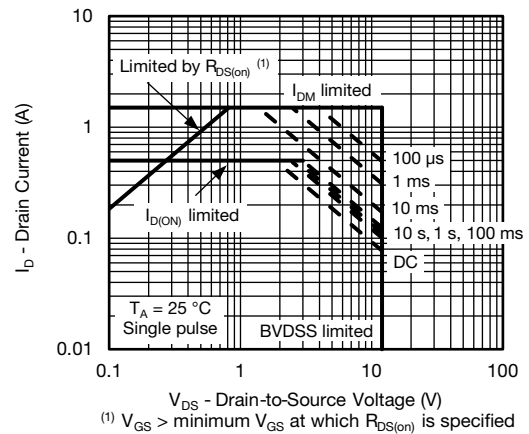
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating <sup>a</sup>



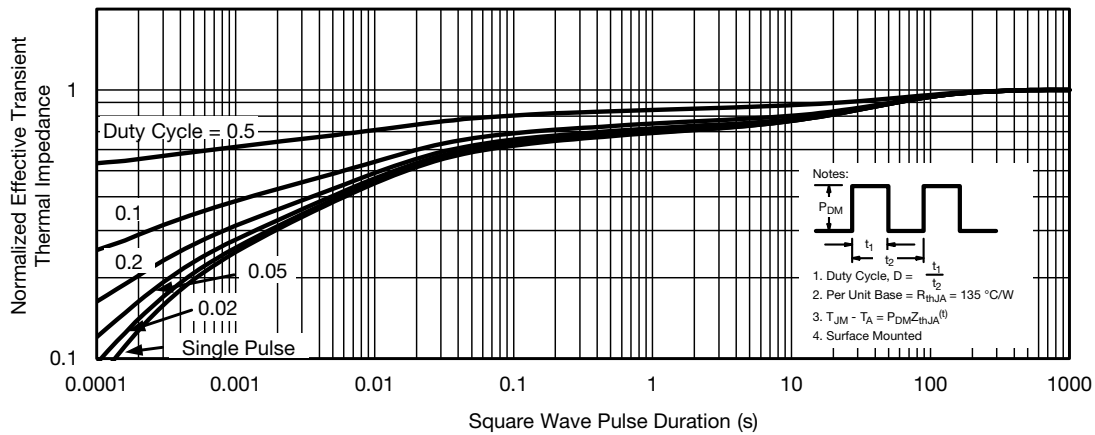
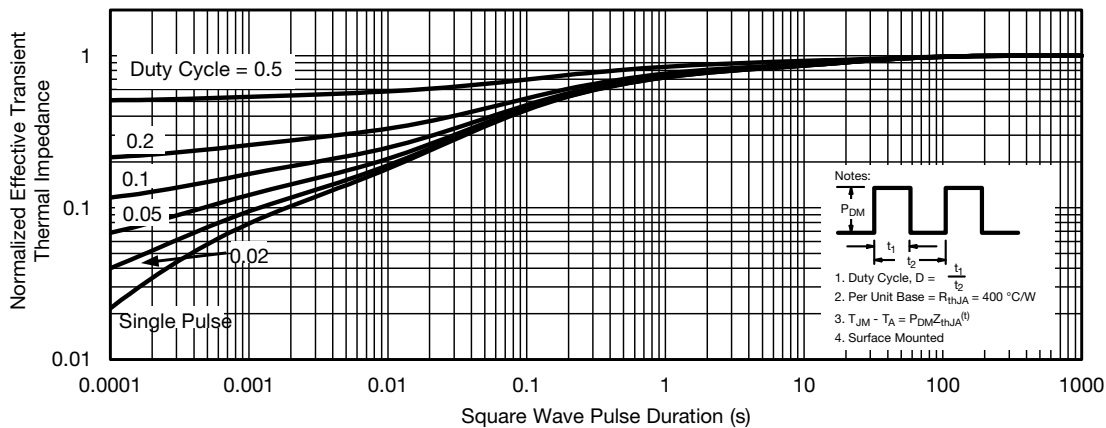
Power, Junction-to-Ambient



Safe Operating Area, Junction-to-Ambient

Note

- a. The power dissipation  $P_D$  is based on  $T_J$  max. = 25 °C, using junction-to-ambient thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Normalized Thermal Transient Impedance, Junction-to-Ambient (on 1" x 1" FR4 board with maximum copper)**

**Normalized Thermal Transient Impedance, Junction-to-Ambient (on 1" x 1" FR4 board with minimum copper)**

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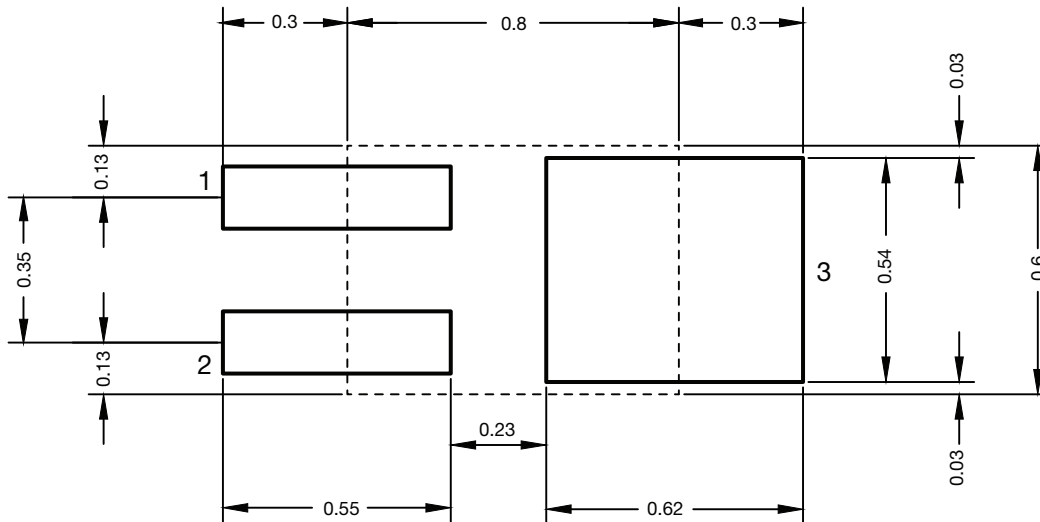
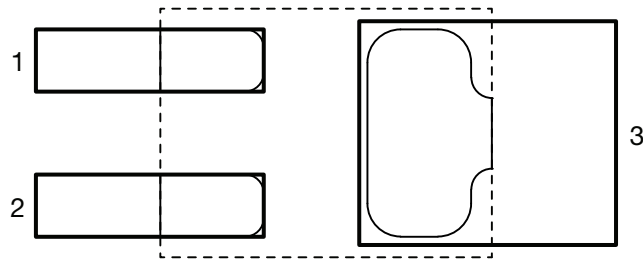
## Case Outline for PowerPAK 0.8 mm x 0.6 mm



DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.350	0.380	0.400	0.0138	0.0150	0.0157
A1	0	-	0.020	0	-	0.0008
b	0.120	0.150	0.180	0.0047	0.0059	0.0071
C	0.119	0.127	0.135	0.0047	0.0050	0.0053
D	0.750	0.800	0.850	0.0295	0.0315	0.0335
D1	0.200	0.250	0.300	0.0078	0.0098	0.0118
E	0.550	0.600	0.650	0.0217	0.0236	0.0256
E1	0.450	0.500	0.550	0.0177	0.0197	0.0217
e	0.300	0.350	0.400	0.0118	0.0138	0.0158
K	0.150	0.250	0.350	0.0058	0.0098	0.0138
L	0.200	0.250	0.300	0.0078	0.0098	0.0118

ECN: C13-1574-Rev. A, 23-Dec-13  
 DWG: 6020

## Recommended Land Pattern PowerPAK® 0806







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